ISO1176T 具有集成变压器驱动器的隔离式 Profibus RS-485 收发器

1 特性

- 符合或超出 EN 50170 和 TIA/EIA-485 的要求
- 信号传输速率高达 40Mbps
- 使用集成变压器驱动器轻松进行隔离式电源设计
- 效率典型值 > 60% (I_{LOAD} = 100mA)，参阅 SLUU471
- 差分输出超过 2.1V（54Ω 负载）
- 低总线电容：10pF（最大值）
- 针对总线开路、短路及空闲状态的失效防护接收器
- 50kV/μs 瞬态抗扰度，典型值
- 安全及管理批准
  - 符合 DIN EN IEC 60747-17 (VDE 0884-17) 标准的 4242V_{PK} 基本绝缘
  - 符合 UL 1577 标准且长达 1 分钟的 2500V_{RMS} 隔离
  - CSA 60950-1 和 CSA 61010-1 标准

2 应用

- Profibus®
- 工厂自动化
- 联网传感器
- 电机/运动控制
- 暖通空调 (HVAC) 及楼宇自动化网络
- 联网保密站 (Networked Security Stations)

3 说明

ISO1176T 是一款隔离式差分线路收发器，集成有用于为隔离变压器提供初级电压的振荡器输出。由于接地环路断开，该器件能够在大得多的共模电压范围内运行，非常适合于远距离传输线路。

经测试，该器件的对称隔离栅可在总线收发器和逻辑电平接口之间提供符合 VDE 标准且长达 60 秒的 4242V_{PK} 隔离。

电隔离差分总线收发器是集成电路，旨在实现多点总线传输线路上的双向数据通信。该收发器将电隔离差分线路驱动器和差分输入线路接收器相结合。驱动器在 ISODE 引脚（引脚 10）上具有高电平有效使能和隔离式使能状态输出，有助于控制方向。驱动器差分输出端和接收器差分输入端在内部连接以形成差分输入/输出 (I/O) 总线端口，该端口用于在禁用驱动器或 V_{CC2} = 0 时为总线提供最小负载。

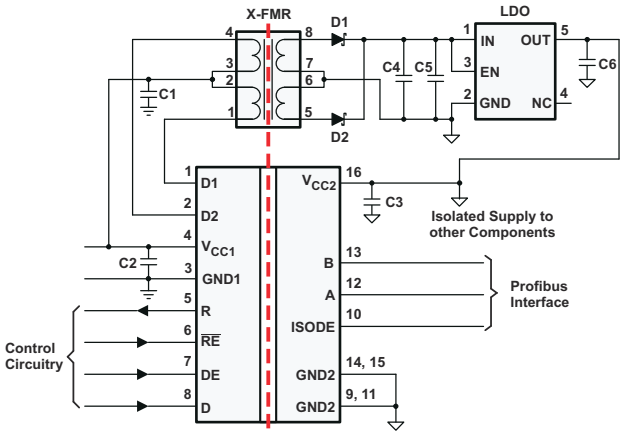
所有带连线的 I/O 都容易遭受来自各种信号源的电瞬态噪声。这些瞬态噪声如果具有足够的幅度和持续时间，就有可能导致收发器和/或邻近的敏感电路受到损坏。ISO1176T 可显著降低数据损坏和成本高昂的控制电路损坏风险。

该器件可在 –40°C 至 85°C 的环境温度范围内运行。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
ISO1176T	SOIC (16)	10.30mm x 7.50mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



典型应用

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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision G (October 2015) to Revision H (August 2023) **Page**

- 将 VDE 标准更改为 DIN EN IEC 60747-17 (VDE 0884-17).....1
- Updated Thermal Characteristics, Safety Limiting Values, and Thermal Derating Curves to provide more accurate system-level thermal calculations.....7
- Updated electrical and switching characteristics to match device performance.....8

Changes from Revision F (October 2012) to Revision G (October 2015) **Page**

- 添加了 *引脚配置和功能* 部分、*ESD 等级* 表、*特性说明* 部分、*器件功能模式*、*应用和实施* 部分、*电源相关建议* 部分、*布局* 部分、*器件和文档支持* 部分以及 *机械、封装和可订购信息* 部分.....1
- 将 VDE 标准更改为 DIN V VDE V 0884-10 (VDE V 0884-10):2006-12.....1

Changes from Revision E (August 2011) to Revision F (October 2012) **Page**

- Changed From "ISO1176T Reference Design SLLU471" To: "ISO1176T Reference Design SLUU471".....32

Changes from Revision D (May 2011) to Revision E (August 2011) **Page**

- Deleted the MIN and MAX values for t_{r_D}, t_{f_D} and t_{BBM} specifications in the Transformer Driver Characteristics table.....11
- Changed test conditions from 1.9 V to 2.4 V, and changed TYP value from 230 to 350 for f_{St} specification in the Transformer Driver Characteristics table.....11

Changes from Revision C (February 2011) to Revision D (May 2011) **Page**

- 添加了图 9-2 1

- Moved the Pin Description closer to the Pin drawing..... 4

5 Pin Configuration and Functions

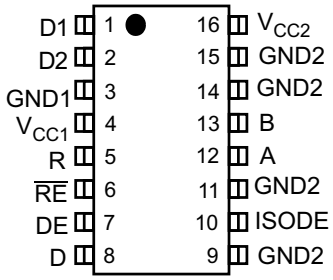


图 5-1. DW Package 16-Pin SOIC Top View

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
A	12	I/O	Non-inverting Driver Output / Receiver Input
B	13	I/O	Inverting Driver Output / Receiver Input
D	8	I	Driver Input
D1	1	O	Transformer Driver Terminal 1, Open Drain Output
D2	2	O	Transformer Driver Terminal 2, Open Drain Output
DE	7	I	Driver Enable Input
GND1	3	—	Logic-side Ground
GND2	9, 11, 14, 15	—	Bus-side Ground. All pins are internally connected.
ISODE	10	O	Bus-side Driver Enable Output Status
R	5	O	Receiver Output
$\overline{RE}$	6	I	Receiver Enable Input. This pin has complementary logic.
V_{CC1}	4	—	Logic-side Power Supply
V_{CC2}	16	—	Bus-side Power Supply

6 Specifications

6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(2)	V_{CC1}, V_{CC2}	-0.5	6	V
V_O	Voltage at any bus I/O terminal		-9	14	V
	Voltage at D1, D2			14	V
V_I	Voltage input	D, DE or $\overline{RE}$	-0.5	6	V
I_O	Receiver output current	Receiver output current	-10	10	mA
I_{D1}, I_{D2}	Transformer Driver Output Current			450	mA
T_J	Junction temperature			150	℃
T_{stg}	Storage temperature		-65	150	℃

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values except differential I/O bus voltages are with respect to the referenced network ground terminal and are peak voltage values.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$ Electrostatic Discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	Bus pins and GND1	±6000	V
		Bus pins and GND2	±10000	V
		All pins	±4000	V
	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)		±1500	V
	Machine model (MM), ANSI/ESDS5.2-1996		±200	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT
V_{CC}	Logic-side supply voltage, V_{CC1} (with respect to GND1)		3		5.5	V
V_{CC}	Bus-side supply voltage, V_{CC2} (with respect to GND2)		4.75		5.25	V
V_{CM}	Voltage at either bus I/O terminal	A or B	-7		12	V
V_{IH}	High-level input voltage	PV, $\overline{RE}$	2		5.5	V
V_{IH}	High-level input voltage	D, DE	0.7*V_{CC1}			V
V_{IL}	Low-level input voltage	PV, $\overline{RE}$	0		0.8	V
V_{IL}	Low-level input voltage	D, DE			0.3*Vcc	V
V_{ID}	Differential input voltage	A with respect to B	-12		12	V
I_O	Output current	Driver	-70		70	mA
I_O	Output current	Receiver	-8		8	mA
T_A	Ambient temperature		-40		85	°C

			MIN	NOM	MAX	UNIT
1 / t_{UI}	Signaling Rate				40	Mbps

6.4 Thermal Information

THERMAL METRIC[1]		ISO1176T DW (SOIC) 16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	76	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	37.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	44.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	13.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter	37.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	-	°C/W

(1) For more information about traditional and new thermal metrics, see the no.

6.5 Power Ratings

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_D	Maximum power dissipation (both sides)	V_{CC1} = V_{CC2} = 5.25 V, T_J = 150°C, C_L = 15 pF, Input at 20 MHz 50% duty cycle square wave			719	mW

6.6 Insulation Specifications

PARAMETER		TEST CONDITIONS	VALUE DW-16	UNIT
CLR	External clearance[1]	Shortest terminal-to-terminal distance through air	8	mm
CPG	External creepage[1]	Shortest terminal-to-terminal distance across the package surface	8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	8	um
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	>400	V
	Material group	According to IEC 60664-1	II	
	Overvoltage category per IEC 60664-1	Rated mains voltage ⩽ 150 V_{RMS}	I-IV	
		Rated mains voltage ⩽ 300 V_{RMS}	I-III	
DIN EN IEC 60747-17 (VDE 0884-17) [2]				
V_{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	566	V_{PK}
V_{IOTM}	Maximum transient isolation voltage	V_{TEST} = V_{IOTM}, t = 60 s (qualification); V_{TEST} = 1.2 x V_{IOTM}, t= 1 s (100% production)	4242	V_{PK}
q_{pd}	Apparent charge[3]	Method b; At routine test (100% production) V_{ini} = 1.2 x V_{IOTM}, t_{ini} = 1 s; $V_{pd(m)}$ = 1.5 x V_{IORM}, t_m = 1 s	⩽5	pC
C_{IO}	Barrier capacitance, input to output[4]	V_{IO} = 0.4 x sin (2 π ft), f = 1 MHz	2	pF
C_I	Input capacitance to ground	V_I = VCC/ 2 + 0.4×sin(2 π ft), f = 1 MHz, VCC = 5 V	2	pF
R_{IO}	Isolation resistance[4]	V_{IO} = 500 V, T_A = 25°C	>10^{12}	Ω
		V_{IO} = 500 V, T_S = 150°C	>10^9	
	Pollution degree		2	
	Climatic category		40/085/21	
UL 1577				

PARAMETER		TEST CONDITIONS	VALUE	UNIT
			DW-16	
V_{ISO}	Maximum withstanding isolation voltage	$V_{TEST} = V_{ISO}$, t = 60 s (qualification), $V_{TEST} = 1.2 \times V_{ISO}$, t = 1 s (100% production)	2500	V_{RMS}

(1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed-circuit board are used to help increase these specifications.
(2) This coupler is suitable for *basic electrical insulation* only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
(3) Apparent charge is electrical discharge caused by a partial discharge (pd).
(4) All pins on each side of the barrier tied together creating a two-terminal device.

6.7 Safety-Related Certifications

VDE	CSA	UL
Certified according to DIN EN IEC 60747-17 (VDE 0884-17)	Certified according to IEC 60950-1 and IEC 61010-1	Certified according to UL 1577 Component Recognition Program
Basic Insulation Maximum Transient Isolation Voltage, 4242 V_{PK} Maximum Surge Isolation Voltage, 4000 V_{PK} Maximum repetitive peak isolation Voltage, 566 V_{PK}	3000 V_{RMS} Isolation Rating; Reinforced insulation per CSA 61010-1 and IEC 61010-1 150 V_{RMS} working voltage; Basic insulation per CSA 61010-1 and IEC 61010-1 600 V_{RMS} working voltage; Basic insulation per CSA 60950-1 and IEC 60950-1 760 V_{RMS} working voltage	Single protection, 2500 V_{RMS}
Certificate number: 40047657	Master contract number: 220991	File number: E181974

6.8 Safety Limiting Values

Safety limiting(1) intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
DW-16 PACKAGE						
I_S	Safety input, output, or supply current	$R_{\theta JA}$ = 76°C/W, V_I = 5.5 V, T_J = 150°C, T_A = 25°C,			299	mA
T_S	Maximum safety temperature				150	°C

(1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power respectively. The maximum limits of I_S and P_S should not be exceeded. These limits vary with the ambient temperature, T_A.
The junction-to-air thermal resistance, $R_{\theta JA}$, in the table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter:
$T_J = T_A + R_{\theta JA} \times P$, where P is the power dissipated in the device.
$T_{J(max)} = T_S = T_A + R_{\theta JA} \times P_S$, where $T_{J(max)}$ is the maximum allowed junction temperature.
$P_S = I_S \times V_I$, where V_I is the maximum input voltage.

6.9 Electrical Characteristics: ISODE-Pin

All typical specs are at V_{CC1}=3.3V, V_{CC2}=5V, T_A=27°C, (Min/Max specs are over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = – 8 mA	V_{CC2} – 0.8	4.6		V
		I_{OH} = – 20 μA	V_{CC2} – 0.1	5		V
V_{OL}	Low-level output voltage	I_{OL} = – 8 mA		0.2	0.4	V
		I_{OL} = – 20 μA		0	0.1	V

6.10 Electrical Characteristics: Driver

All typical specs are at V_{CC1}=3.3V, V_{CC2}=5V, T_A=27°C, (Min/Max specs are over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$\|V_{OD}\|$	Open-circuit differential output voltage	$\|V_A-V_B\|$, Figure 9	1.5		V_{CC2}	V
$\|V_{OD(SS)}\|$	Steady state differential output voltage magnitude	See Figure 10 and Figure 14	2.1			V
	Steady state differential output voltage magnitude	Common mode loading with V_{test} from -7V to 12V, See figure 10	2.1			V
$\Delta\|V_{ODSS}\|$	Change in differential output voltage between two states	R_L = 54 ohms, See Figure 12 and Figure 13	-200		200	mV
$V_{OC(SS)}$	Steady state common-mode output voltage	R_L = 54 ohms, See Figure 12 and Figure 13	2		3	V
$\Delta V_{OC(SS)}$	change in steady-state common-mode output voltage between two states	R_L = 54 ohms, See Figure 12 and Figure 13	-200		200	mV
$V_{OC(PP)}$	Peak-to-peak common-mode output voltage	R_L = 54 ohms, See Figure 12 and Figure 13		0.5		V
$V_{OD(RING)}$	Differential output voltage over and undershoot	See Figure 14 and Figure 17			10	$\%V_{OD(PP)}$
I_I	Input current	D, DE at 0 V or V_{CC1}	-10		10	µA
$I_{O(OFF)}$	Output current with power off	Vcc_2 = 0 V	See receiver input current			µA
I_{OZ}	High-impedance state output current	DE at 0 V	See receiver input current			µA
$I_{OS(P)}$	Peak short circuit output current	DE at V_{CC}, See Figure 15 and Figure 16: V_{OS} = -7 to 12 V	-250		250	mA
$I_{OS(SS)}$	Steady state short-circuit output current	DE at V_{CC}, See Figure 15 and Figure 16: V_{OS} = 12 V, D at GND1			150	mA
		DE at V_{CC}, See Figure 15 and Figure 16: V_{OS} = -7 V, D at V_{CC1}	-150			mA
C_{OD}	Differential output capacitance			7	18.8	pF
CMTI	Common-mode transient immunity	See Figure 27	25			kV/µs

6.11 Electrical Characteristics: Receiver

All typical specs are at V_{CC1}=3.3V, V_{CC2}=5V, T_A=27°C, (Min/Max specs are over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IT+}	Positive-going input threshold voltage	I_O = -8 mA, See Figure 22		-80	-10	mV
V_{IT-}	Negative-going input threshold voltage	I_O = 8 mA, See Figure 22	-200	-120		mV
V_{hys}	Input hysteresis (V_{IT+} - V_{IT-})			40		mV
V_{OH}	Output Voltage	V_{CC1} at 3.3 V and V_{CC2} at 5V, V_{ID} = 200mV, I_O = -8mA	V_{CC1}-0.4	3		V
V_{OH}	Output Voltage	V_{CC1} at 3.3 V and V_{CC2} at 5V, V_{ID} = 200mV, I_O = -20uA	V_{CC1}-0.1	3.3		V
V_{OL}	Output Voltage	V_{CC1} at 3.3 V and V_{CC2} at 5V, V_{ID} = -200mV, I_O = 8mA		0.2	0.4	V
V_{OL}	Output Voltage	V_{CC1} at 3.3 V and V_{CC2} at 5V, V_{ID} = -200mV, I_O = 20uA		0	0.1	V
V_{OH}	Output Voltage	V_{CC1} at 5 V and V_{CC2} at 5V, V_{ID} = 200mV, I_O = -8mA	V_{CC1}-0.8	4.6		V
V_{OH}	Output Voltage	V_{CC1} at 5 V and V_{CC2} at 5V, V_{ID} = 200mV, I_O = -20uA	V_{CC1}-0.1	5		V
V_{OL}	Output Voltage	V_{CC1} at 5 V and V_{CC2} at 5V, V_{ID} = -200mV, I_O = 8mA		0.2	0.4	V
V_{OL}	Output Voltage	V_{CC1} at 5 V and V_{CC2} at 5V, V_{ID} = -200mV, I_O = 20uA		0	0.1	V

All typical specs are at V_{CC1}=3.3V, V_{CC2}=5V, T_A=27°C, (Min/Max specs are over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_A or I_B	Bus pin input current	V_I = -7 V or 12 V, other input = 0V: V_{CC} = 4.75 V or 5.25 V	-160		200	µA
		V_I = -7 V or 12 V, other input = 0V: V_{CC2} = 0 V	-160		200	µA
I_I	Receiver enable input current	$\overline{RE}$ = 0 V or V_{CC1}	-50		50	µA
I_{OZ}	High impedance state output current	$\overline{RE}$ = V_{CC1}	– 1		1	µA
R_{ID}	Differential input resistance	A, B	60			kohm
C_{ID}	Differential input capacitance	Test input signal is a 1.5MHz sine wave with 1V_{PP} amplitude, C_D is measured across A and B		7	18.8	pF
CMR	Common mode rejection	See Figure 26		4		V

6.12 Supply Current

Bus loaded or unloaded (over recommended operating conditions unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DRIVER ENABLED, RECEIVER DISABLED					
I_{CC1} (1)	V_{CC1} = 3.3 V ± 10%, DE, $\overline{RE}$ = 0V or V_{CC1}, No Load		4.5	8	mA
	V_{CC1} = 5 V ± 10%, DE, $\overline{RE}$ = 0V or V_{CC1}, No Load		7	11	mA
I_{CC2} (1)	V_{CC2} = 5 V ± 5%, DE, $\overline{RE}$ = 0V or V_{CC1}, No Load		13.5	18	mA

(1) I_{CC1} and I_{CC2} are measured when device is connected to external power supplies. D1 and D2 are disconnected from external transformer.

6.13 Transformer Driver Characteristics

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{OSC}	Oscillator frequency	V_{CC1} = 5 V ± 10%, D1 and D2 connected to transformer	350	450	610	kHz
		V_{CC1} = 3.3 V ± 10%, D1 and D2 connected to transformer	300	400	550	kHz
R_{ON}	Switch on resistance	D1 and D2 connected to 50 Ω pullup resistors		1	2.5	ohm
t_{r_D}	D1, D2 output rise time	V_{CC1} = 5 V ± 10%, See Figure 28, D1 and D2 connected to 50-Ω pullup resistors		80		ns
		V_{CC1} = 3.3 V ± 10%, See Figure 28, D1 and D2 connected to 50-Ω pullup resistors		70		ns
t_{f_D}	D1, D2 output fall time	V_{CC1} = 5 V ± 10%, See Figure 28, D1 and D2 connected to 50-Ω pullup resistors		55		ns
		V_{CC1} = 3.3 V ± 10%, See Figure 28, D1 and D2 connected to 50-Ω pullup resistors		80		ns
f_{St}	Startup frequency	V_{CC1} = 2.4 V, D1 and D2 connected to transformer		350		kHz
t_{BBM}	Break before make time delay	V_{CC1} = 5 V ± 10%, See Figure 28, D1 and D2 connected to 50-Ω pullup resistors		38		ns
		V_{CC1} = 3.3 V ± 10%, See Figure 28, D1 and D2 connected to 50-Ω pullup resistors		140		ns

6.14 Switching Characteristics: Driver

All typical specs are at V_{CC1}=3.3V, V_{CC2}=5V, T_A=27°C, (Min/Max specs are over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISO1176						
t_{PHL}, t_{PLH}	Propagation delay	V_{CC1} at 5 V, V_{CC2} at 5 V		23	35	ns
tsk(p)	Pulse skew ($\|t_{PHL} - t_{PLH}\|$)	V_{CC1} at 5 V, V_{CC2} at 5 V		2	7.5	ns
t_{PHL}, t_{PLH}	Propagation delay	V_{CC1} at 3.3 V, V_{CC2} at 5 V			40	ns
tsk(p)	Pulse skew ($\|t_{PHL} - t_{PLH}\|$)	V_{CC1} at 3.3 V, V_{CC2} at 5 V		2	7.5	ns
t_r, t_f	Differential output rise time and fall time	See Figure 17	2	3	7.5	ns
t_{pDE}	DE to ISODE prop delay	See Figure 21			30	ns
$t_{t(MLH)}$, $t_{t(MHL)}$	Output transition skew	See Figure 18			1	ns
$t_{P(AZH)}$, $t_{P(BZH)}$, $t_{P(AZL)}$, $t_{P(BZL)}$	Propagation delay, high-impedance-to-active output	C_L = 50 pF, $\overline{RE}$ at 0 V, See Fgure 19 and Figure 20			80	ns
$t_{P(AHZ)}$, $t_{P(BHZ)}$, $t_{P(ALZ)}$, $t_{P(BLZ)}$	Propagation delay time, active-to-high-impedance output	C_L = 50 pF, $\overline{RE}$ at 0 V, See Fgure 19 and Figure 20			80	ns
$\|t_{P(AZL)} - t_{P(BZH)}\|$, $\|t_{P(AZH)} - t_{P(BZL)}\|$	Enable skew time	C_L = 50 pF, $\overline{RE}$ at 0 V, See Fgure 19 and Figure 20		0.55	1.5	ns
$t_{(CFB)}$	Time from application of short-circuit to current foldback	See Figure 16		0.5		µs
$t_{(TSD)}$	Time from application of short-circuit to thermal shutdown	T_A = 25°C, See Figure 16	100			µs

6.15 Switching Characteristics: Receiver

All typical specs are at V_{CC1}=3.3V, V_{CC2}=5V, T_A=27°C, (Min/Max specs are over recommended operating conditions unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISO1176						
t_{PHL}, t_{PLH}	Propagation delay	V_{CC1} at 5 V, V_{CC2} at 5 V			50	ns
tsk(p)	Pulse skew ($\|t_{PHL} - t_{PLH}\|$)	V_{CC1} at 5 V, V_{CC2} at 5 V		2	7.5	ns
t_{PHL}, t_{PLH}	Propagation delay	V_{CC1} at 3.3 V, V_{CC2} at 5 V			55	ns
tsk(p)	Pulse skew ($\|t_{PHL} - t_{PLH}\|$)	V_{CC1} at 3.3 V, V_{CC2} at 5 V		2	7.5	ns
t_r, t_f	Differential output rise time and fall time	See Figure 17		2	4	ns
t_{PZH}	Propagation delay time, high-impedance-to-high-level output	DE at V_{CC1}, See Figure 24		13	25	ns
t_{PHZ}	Propagation delay time, high-level-to-high-impedance output	DE at V_{CC1}, See Figure 24		13	25	ns
t_{PZL}	Propagation delay time, high-impedance-to-low-level output	DE at V_{CC}, See Figure 25		13	25	ns
t_{PLZ}	Propagation delay time, low-level-to-high-impedance output	DE at V_{CC}, See Figure 25		13	25	ns

6.16 Insulation Characteristics Curves

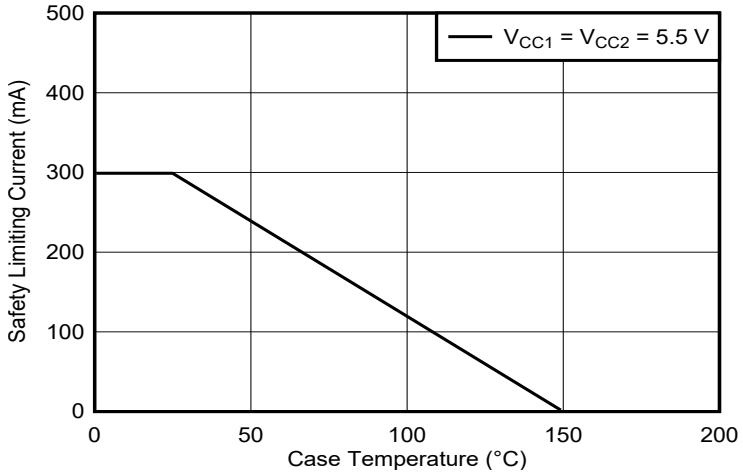


图 6-1. Thermal Derating Curve for Safety Limiting Power for DW-16 Package

6.17 Typical Characteristics

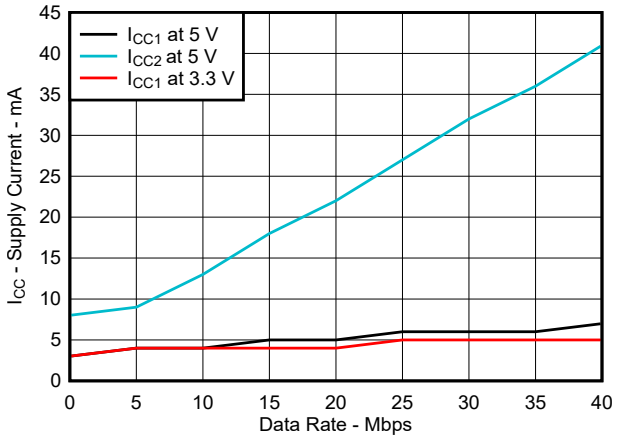
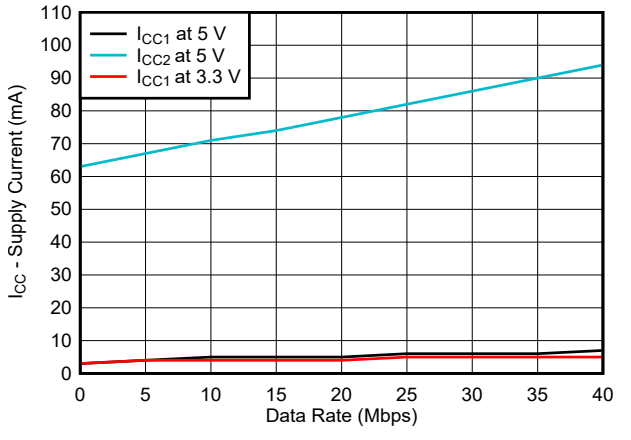


图 6-2. RMS Supply Current (I_{CC1} and I_{CC2}) vs Signaling Rate With No Load



R_L = 54 Ω C_L = 50 pF T_A = 25°C

图 6-3. RMS Supply Current (I_{CC1} and I_{CC2}) vs Signaling Rate With Load

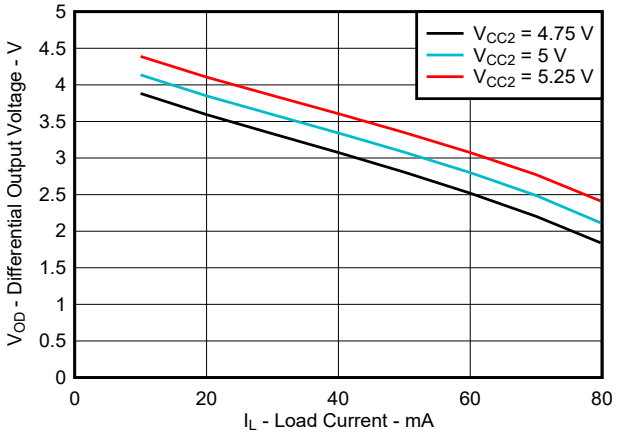
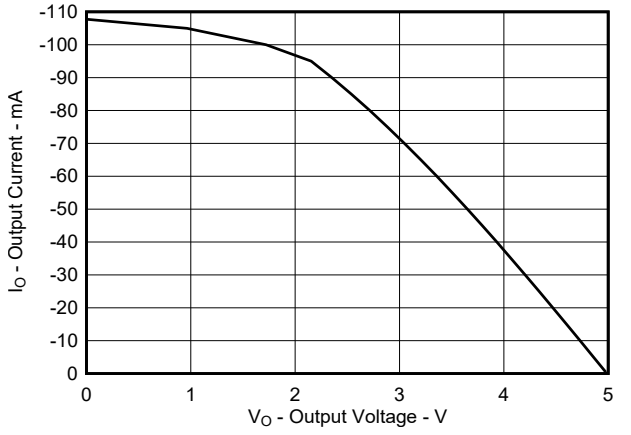


图 6-4. Differential Output Voltage vs Load Current



C_L = 50 pF T_A = 25°C

图 6-5. Receiver High-Level Output Voltage Vs High-Level Output Current

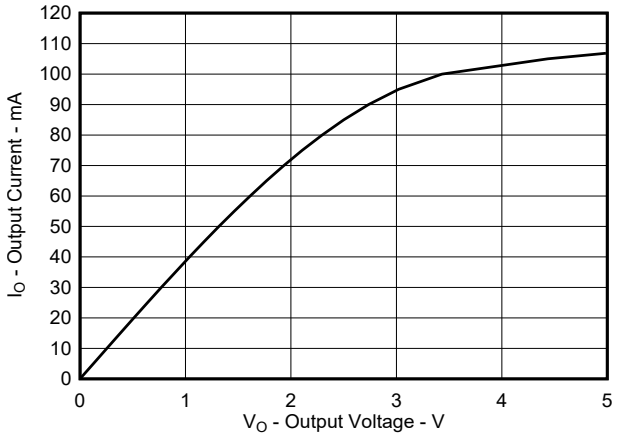


图 6-6. Receiver Low-Level Output Voltage vs Low-Level Output Current

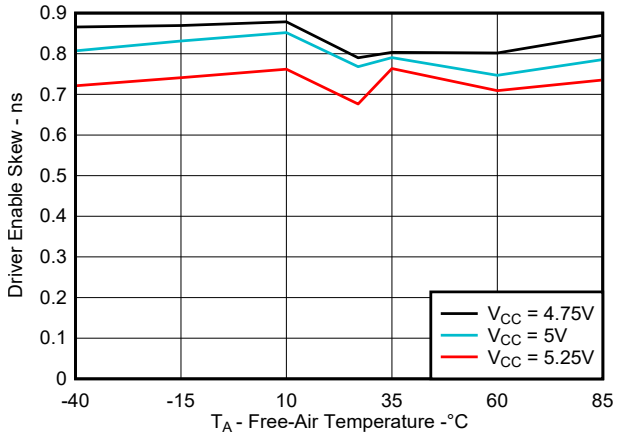


图 6-7. Driver Enable Skew vs Free-Air Temperature

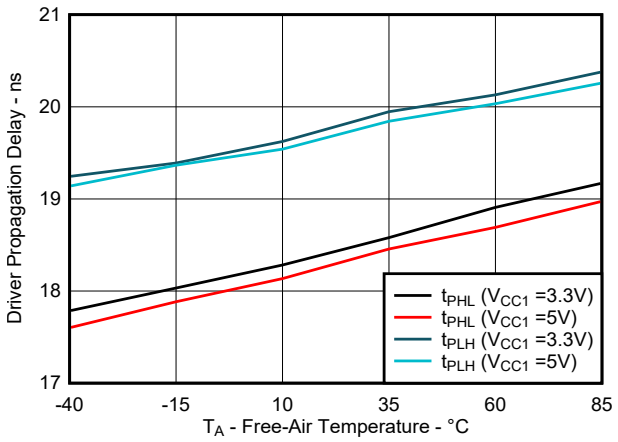


图 6-8. Driver Propagation Delay vs Free-Air Temperature

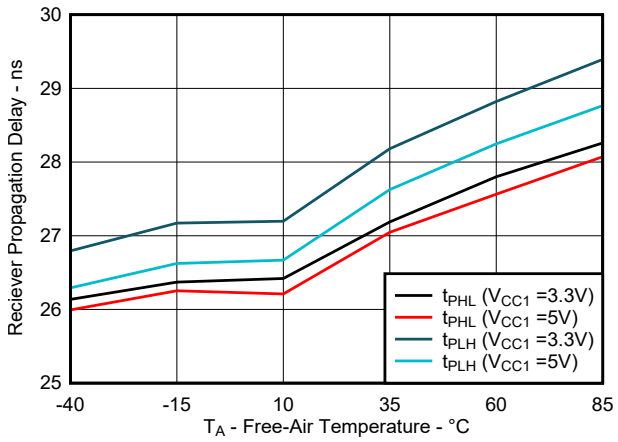


图 6-9. Receiver Propagation Delay vs Free-Air Temperature

7 Parameter Measurement Information

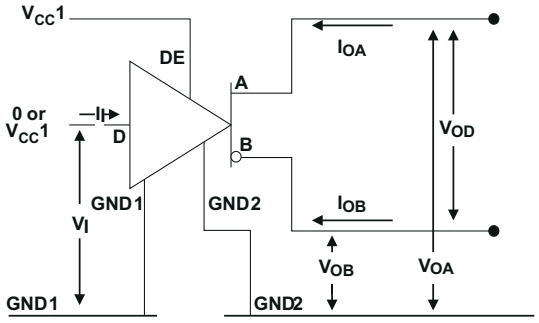


图 7-1. Open Circuit Voltage Test Circuit

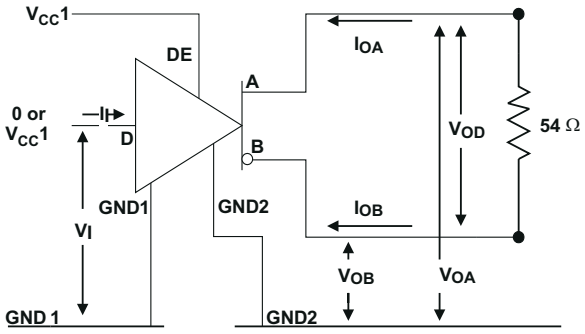


图 7-2. V_{OD} Test Circuit

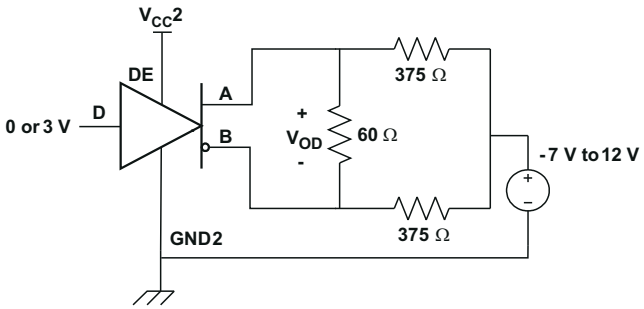


图 7-3. Driver V_{OD} with Common-mode Loading Test Circuit

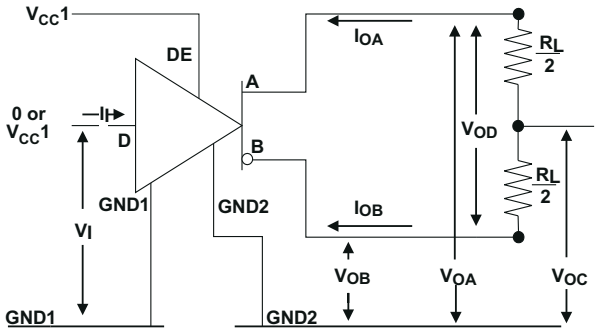


图 7-4. Driver V_{OD} and V_{OC} Without Common-Mode Loading Test Circuit

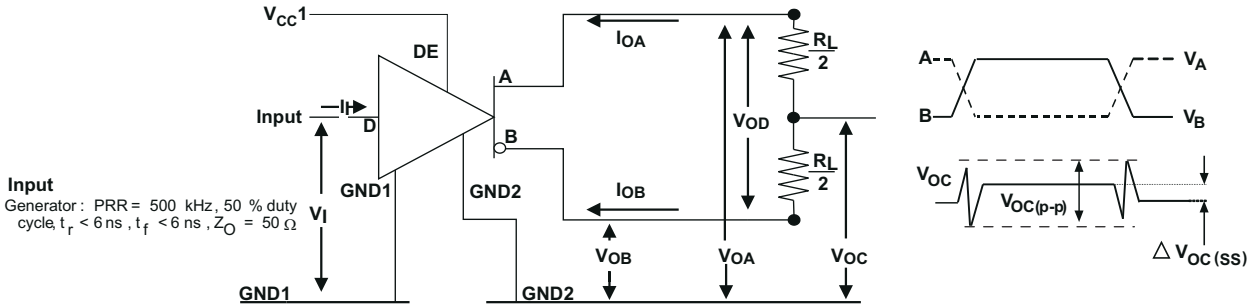


图 7-5. Steady-State Output Voltage Test Circuit and Voltage Waveforms

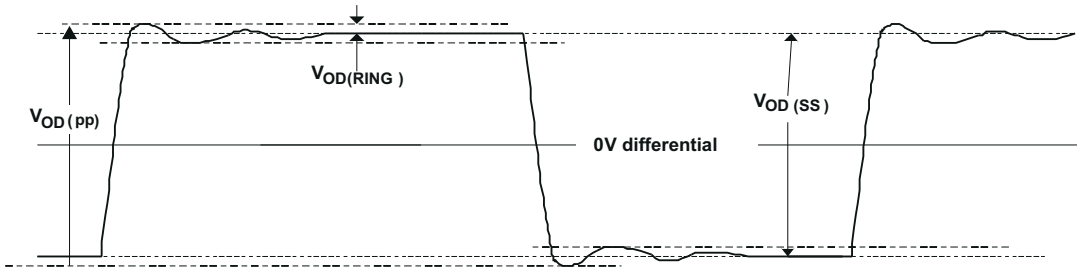


图 7-6. $V_{OD(RING)}$ Waveform and Definitions

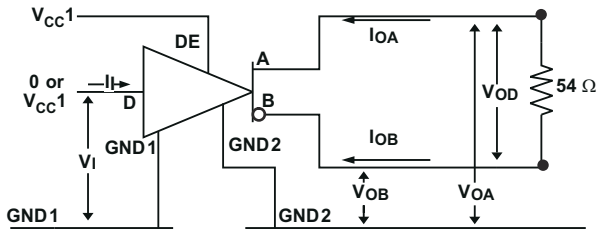


图 7-7. Input Voltage Hysteresis Test Circuit

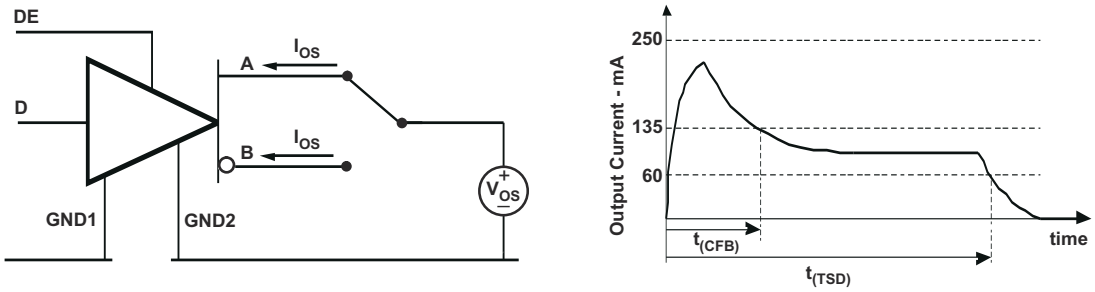


图 7-8. Driver Short-Circuit Test Circuit and Waveforms (Short Circuit applied at Time t=0)

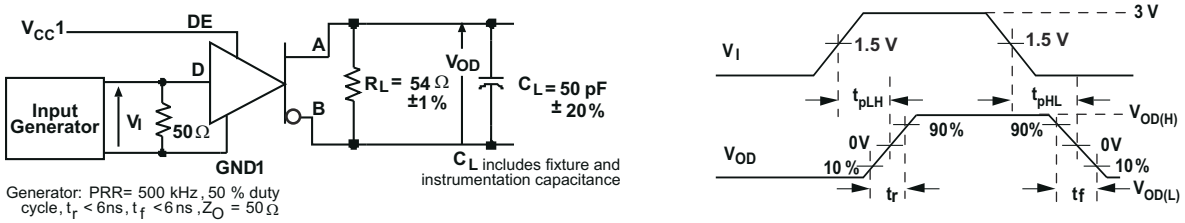


图 7-9. Driver Switching Test Circuit and Waveforms

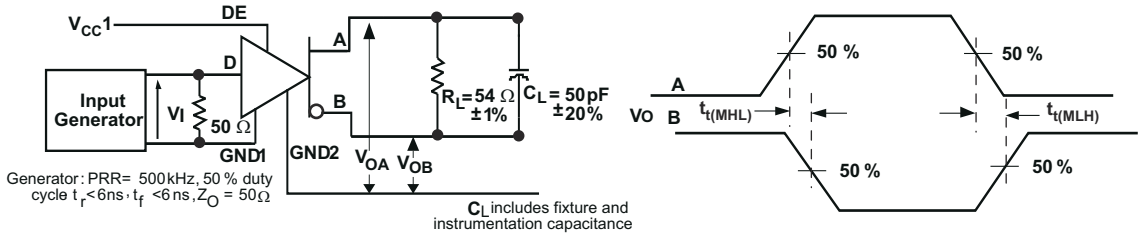


图 7-10. Driver Output Transition Skew Test Circuit and Waveforms

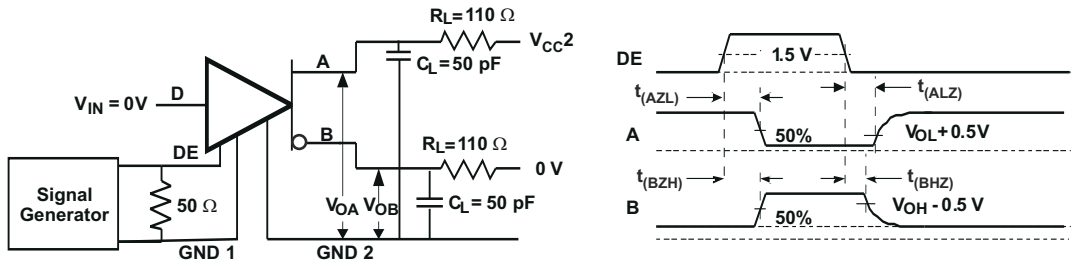


图 7-11. Driver Enable/Disable Test, D at Logic Low Test Circuit and Waveforms

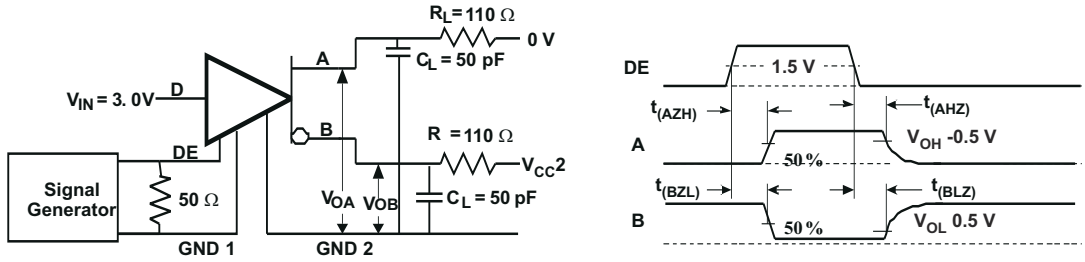


图 7-12. Driver Enable/Disable Test, D at Logic High Test Circuit and Waveforms

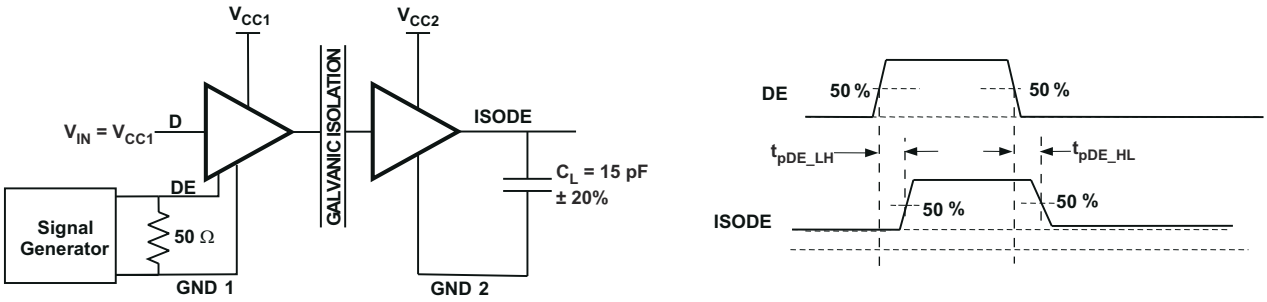


图 7-13. DE to ISODE Prop Delay Test Circuit and Waveforms

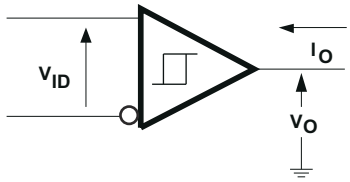


图 7-14. Receiver DC Parameter Definitions

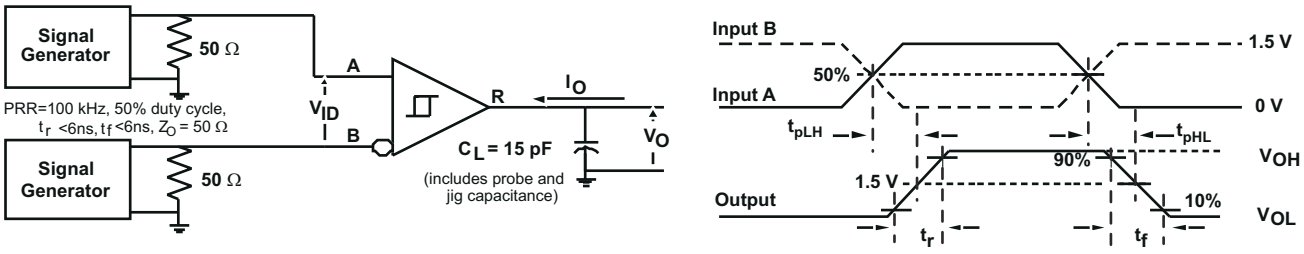


图 7-15. Receiver Switching Test Circuit and Waveforms

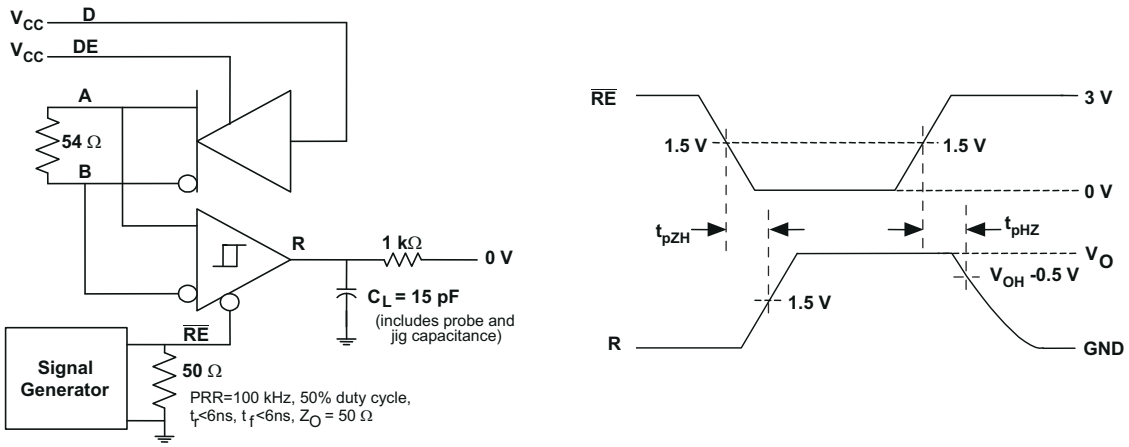


图 7-16. Receiver Enable Test Circuit and Waveforms, Data Output High

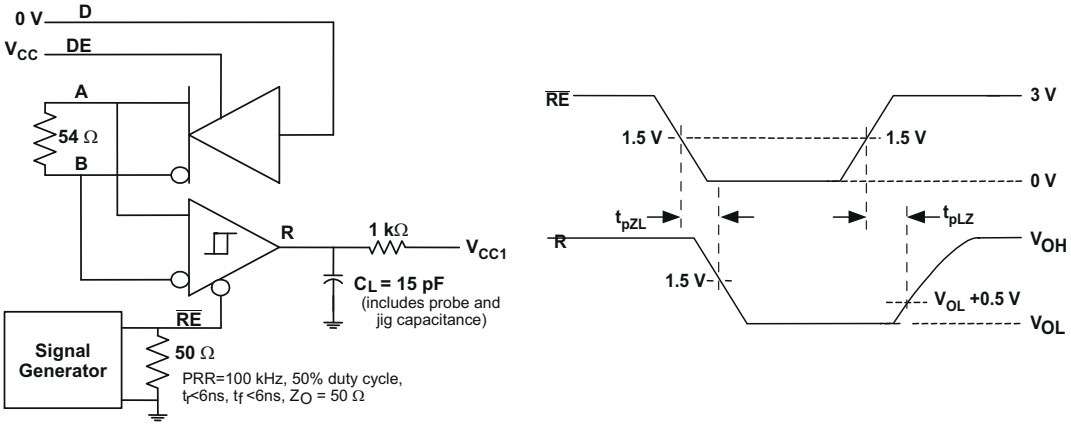


图 7-17. Receiver Enable Test Circuit and Waveforms, Data Output Low

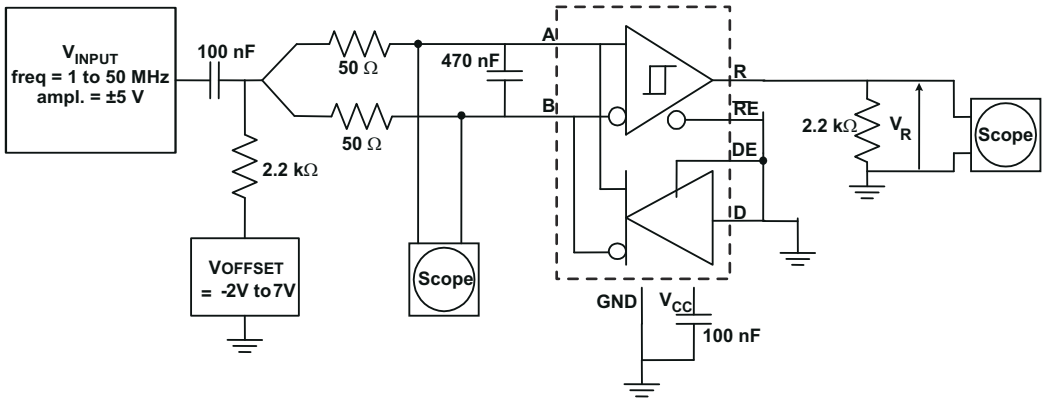


图 7-18. Common-Mode Rejection Test Circuit

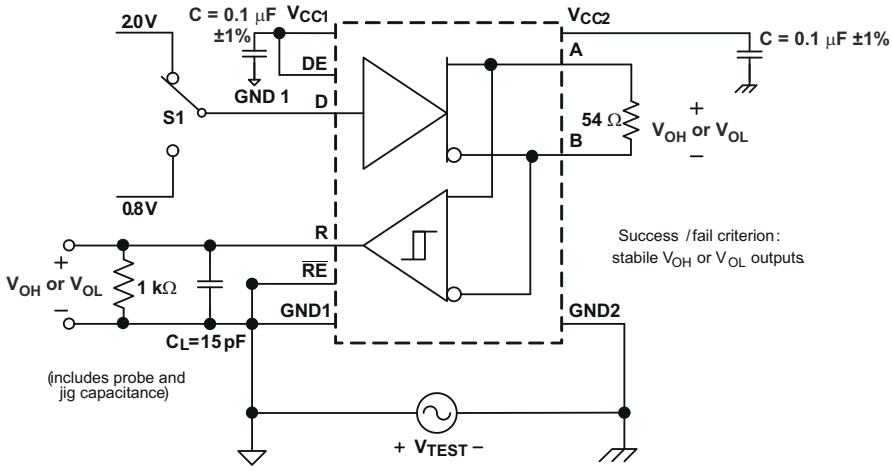


图 7-19. Common-Mode Transient Immunity Test Circuit

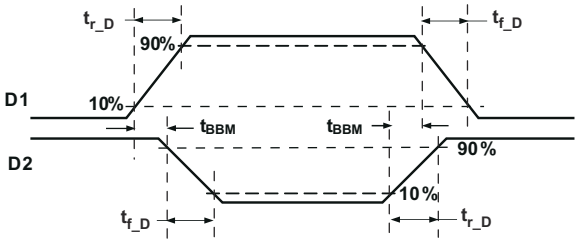


图 7-20. Transition Times and Break-Before-Make Time Delay for D1, D2 Outputs

8 Detailed Description

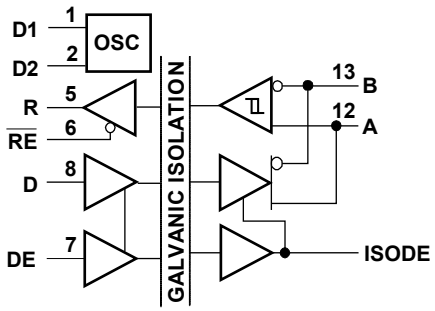
8.1 Overview

The ISO1176T is an isolated half-duplex differential line transceiver that meets the requirements of EN 50170 and TIA/EIA 485/422 applications. It has integrated transformer driver for convenient secondary power supply design. The device is rated to provide galvanic isolation of up to 4242 V_{PK} per VDE and 2500 V_{RMS} per UL 1577. The device has active-high driver enable and active-low receiver enable functions to control the data flow. It has maximum data transmission speed of 40 Mbps.

When the driver enable pin, DE, is logic high, the differential outputs A and B follow the logic states at data input D. A logic high at D causes A to turn high and B to turn low. In this case, the differential output voltage defined as $V_{OD} = V_{(A)} - V_{(B)}$ is positive. When D is low, the output states reverse, B turns high, A becomes low, and V_{OD} is negative. When DE is low, both outputs turn high-impedance. In this condition, the logic state at D is irrelevant. The DE pin has an internal pulldown resistor to ground, thus when left open the driver is disabled (high-impedance) by default. The D pin has an internal pullup resistor to V_{CC}, thus, when left open while the driver is enabled, output A turns high and B turns low.

When the receiver enable pin, $\overline{RE}$, is logic low, the receiver is enabled. When the differential input voltage defined as $V_{ID} = V_{(A)} - V_{(B)}$ is positive and higher than the positive input threshold, V_{IT+}, the receiver output, R, turns high. When V_{ID} is negative and lower than the negative input threshold, V_{IT-}, the receiver output, R, turns low. If V_{ID} is between V_{IT+} and V_{IT-} the output is indeterminate. When $\overline{RE}$ is logic high or left open, the receiver output is high-impedance and the magnitude and polarity of V_{ID} are irrelevant. Internal biasing of the receiver inputs causes the output to go failsafe-high when the transceiver is disconnected from the bus (open-circuit), the bus lines are shorted (short-circuit), or the bus is not actively driven (idle bus).

8.2 Functional Block Diagram



8.3 Device Functional Modes

表 8-1 and 表 8-2 are the function tables for the ISO1176T driver and receiver.

表 8-1. Driver Function Table(1)

V_{CC1}	V_{CC2}	INPUT (D)	ENABLE INPUT (DE)	ENABLE OUTPUT (ISODE)	OUTPUTS	
					A	B
PU	PU	H	H	H	H	L
PU	PU	L	H	H	L	H
PU	PU	X	L	L	Z	Z
PU	PU	X	open	L	Z	Z
PU	PU	open	H	H	H	L
PD	PU	X	X	L	Z	Z
PU	PD	X	X	L	Z	Z
PD	PD	X	X	L	Z	Z

(1) PU = Powered Up, PD = Powered Down, H = High Level, L= Low Level, X = Don't Care, Z = High Impedance (off)

表 8-2. Receiver Function Table(1)

V_{CC1}	V_{CC2}	DIFFERENTIAL INPUT $V_{ID} = (V_A - V_B)$	ENABLE ($\overline{RE}$)	OUTPUT (R)
PU	PU	$-0.01V \leqslant V_{ID}$	L	H
PU	PU	$-0.2V < V_{ID} < -0.01V$	L	?
PU	PU	$V_{ID} \leqslant -0.2V$	L	L
PU	PU	X	H	Z
PU	PU	X	open	Z
PU	PU	Open circuit	L	H
PU	PU	Short Circuit	L	H
PU	PU	Idle (terminated) bus	L	H
PD	PU	X	X	Z
PU	PD	X	L	H
PD	PD	X	X	Z

(1) PU = Powered Up, PD = Powered Down, H = High Level, L= Low Level, X = Don’t Care, Z = High Impedance (off), ? = Indeterminate

8.3.1 Device I/O Schematics

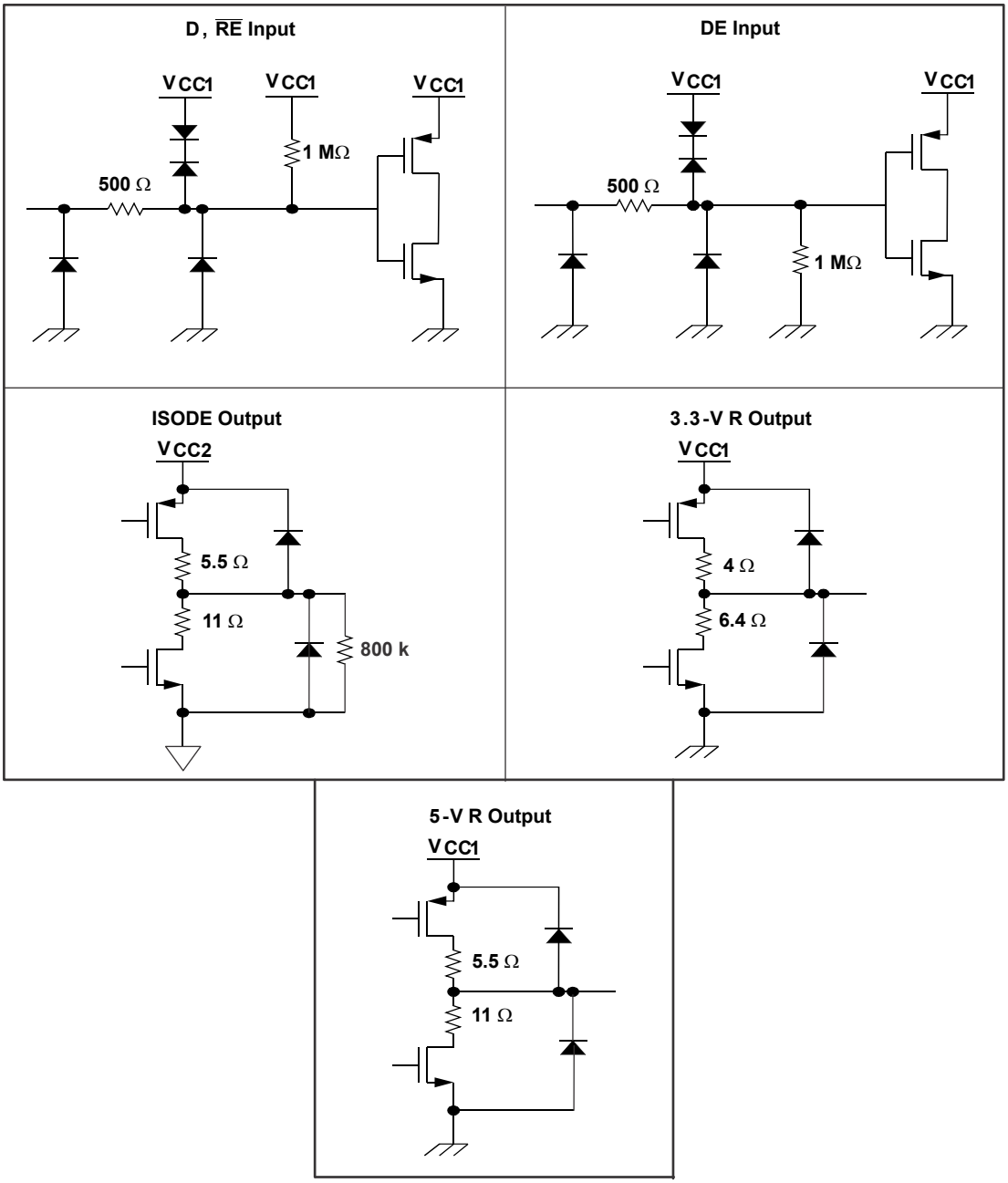


图 8-1. Equivalent Circuit Schematics

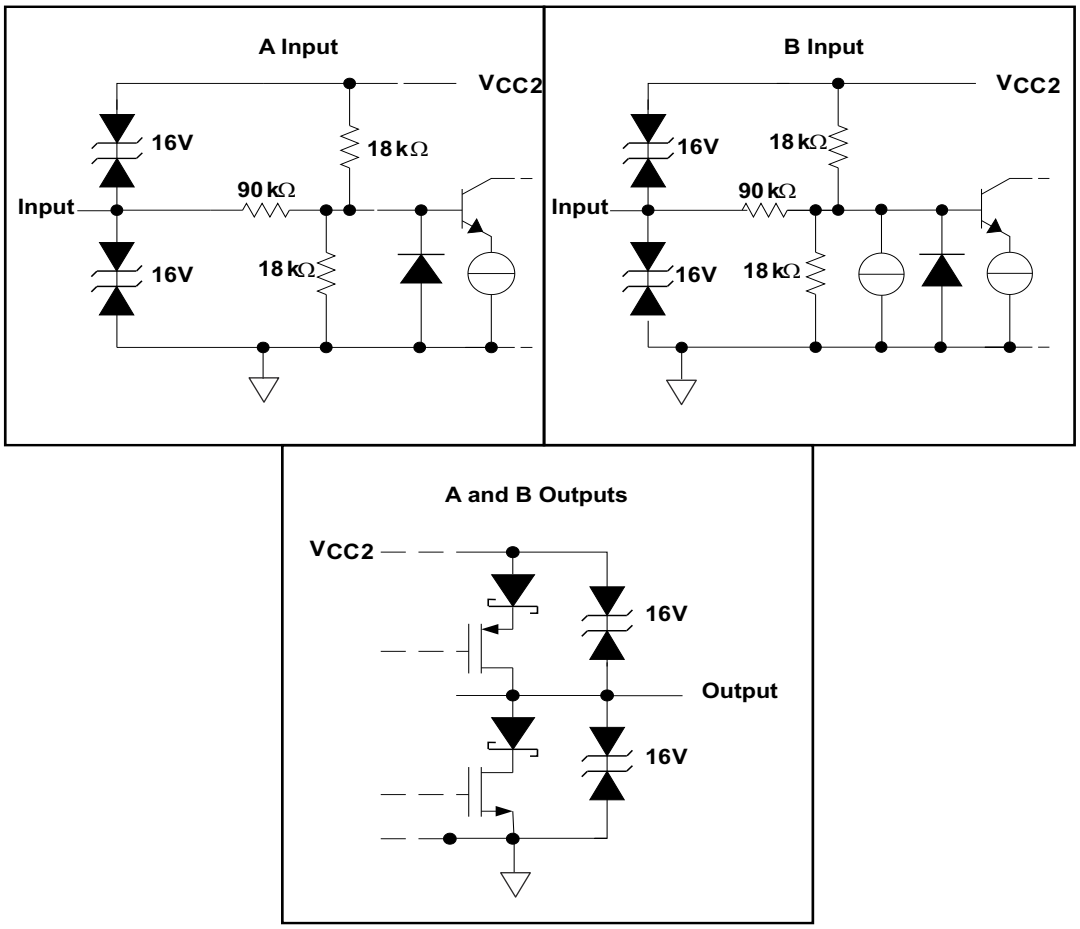


图 8-2. Equivalent Circuit Schematics

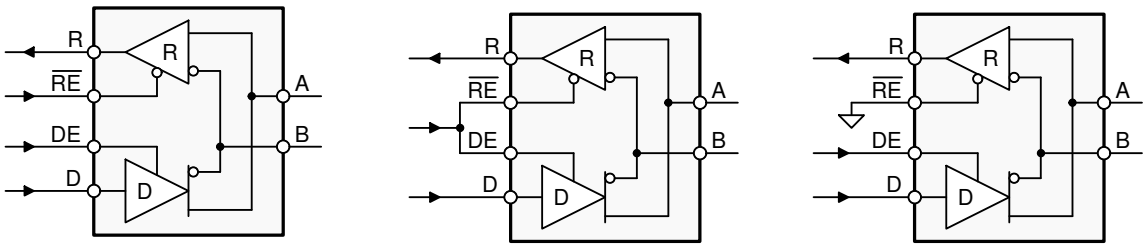
9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客 户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

The ISO1176T device consists of a RS-485 transceiver, commonly used for asynchronous data transmissions. For half-duplex transmission, only one pair is shared for both transmission and reception of data. To eliminate line reflections, each cable end is terminated with a termination resistor, R(T), whose value matches the characteristic impedance, Z0, of the cable. This method, known as parallel termination, allows for higher data rates over longer cable length.



a) Independent driver and receiver enable signals

b) Combined enable signals for use as directional control pin

c) Receiver always on

图 9-1. Half-Duplex Transceiver Configurations

9.2 Typical Application

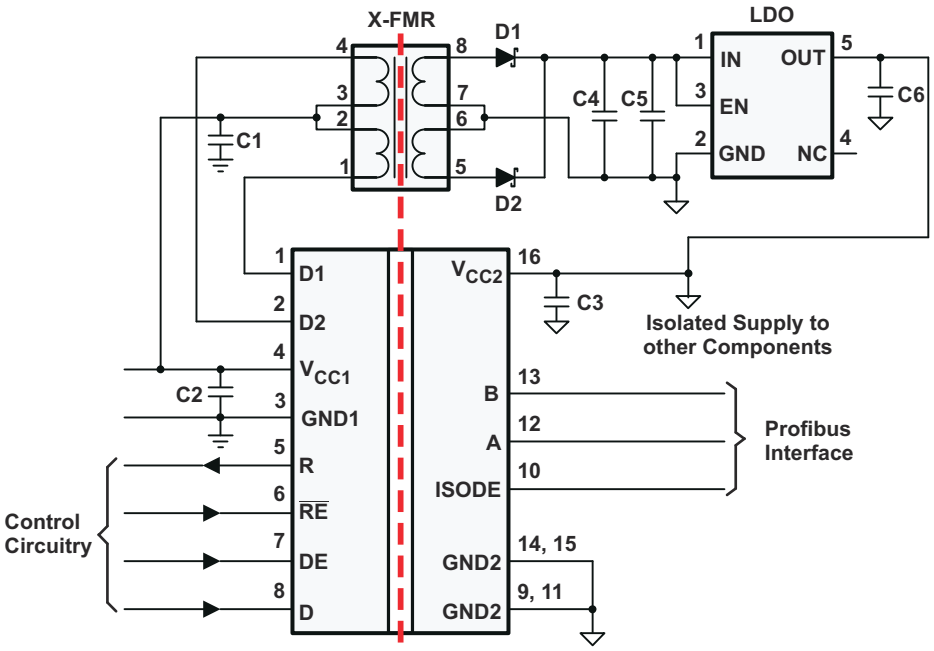


图 9-2. Typical Application

9.2.1 Design Requirements

RS-485 is a robust electrical standard suitable for long-distance networking that may be used in a wide range of applications with varying requirements, such as distance, data rate, and number of nodes.

表 9-1. Design Parameters

PARAMETER	VALUE
Pullup and Pulldown Resistors	1 kΩ to 10 kΩ
Decoupling Capacitors	100 nF

9.2.2 Detailed Design Procedure

9.2.2.1 Transient Voltages

9.2.2.1.1

Isolation of a circuit insulates it from other circuits and earth so that noise develops across the insulation rather than circuit components. The most common noise threat to data-line circuits is voltage surges or electrical fast transients that occur after installation and the transient ratings of ISO1176T are sufficient for all but the most severe installations. However, some equipment manufacturers use their ESD generators to test transient susceptibility of their equipment and can exceed insulation ratings. ESD generators simulate static discharges that may occur during device or equipment handling with low-energy but high voltage transients.

图 9-3 models the ISO1176T bus IO connected to a noise generator. C_{IN} and R_{IN} is the device and any other stray or added capacitance or resistance across the A or B pin to GND2, C_{ISO} and R_{ISO} is the capacitance and resistance between GND1 and GND2 of ISO1176T plus those of any other insulation (transformer, or similar), and we assume stray inductance negligible. From this model, the voltage at the isolated bus return is shown in 方程式 1:

$$v_{GND2} = v_N \frac{Z_{ISO}}{Z_{ISO} + Z_{IN}} \tag{1}$$

and will always be less than 16 V from V_N. If ISO1176T is tested as a stand-alone device, $R_{IN} = 6 \times 10^4\ \Omega$, $C_{IN} = 16 \times 10^{-12}$ F, $R_{ISO} = 10^9\ \Omega$ and $C_{ISO} = 10^{-12}$ F.

Note from 图 9-3 that the resistor ratio determines the voltage ratio at low frequency and it is the inverse capacitance ratio at high frequency. In the stand-alone case and for low frequency, as shown in 方程式 2,

$$\frac{v_{GND2}}{v_N} = \frac{R_{ISO}}{R_{ISO} + R_{IN}} = \frac{10^9}{10^9 + 6 \times 10^4} \tag{2}$$

or essentially all of noise appears across the barrier. At high frequency, as shown in 方程式 3,

$$\frac{v_{GND2}}{v_N} = \frac{\frac{1}{C_{ISO}}}{\frac{1}{C_{ISO}} + \frac{1}{C_{IN}}} = \frac{1}{1 + \frac{C_{ISO}}{C_{IN}}} = \frac{1}{1 + \frac{1}{16}} = 0.94 \tag{3}$$

and 94% of V_N appears across the barrier. As long as R_{ISO} is greater than R_{IN} and C_{ISO} is less than C_{IN}, most of transient noise appears across the isolation barrier, as it should.

We recommend the reader not test equipment transient susceptibility with ESD generators or consider product claims of ESD ratings above the barrier transient ratings of an isolated interface. ESD is best managed through recessing or covering connector pins in a conductive connector shell and installer training.

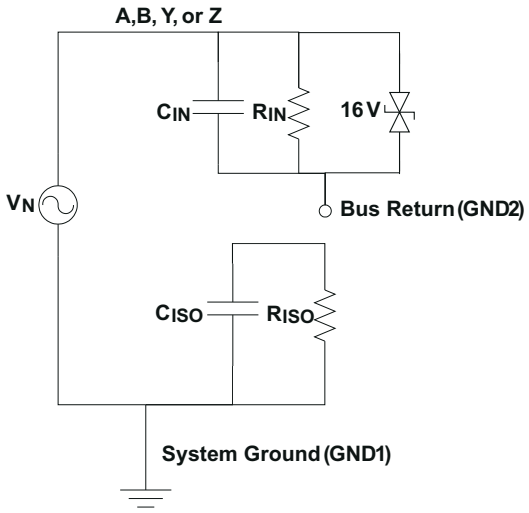


图 9-3. Noise Model

9.2.3 Application Curve

At maximum working voltage, ISO1176T isolation barrier has more than 28 years of life.

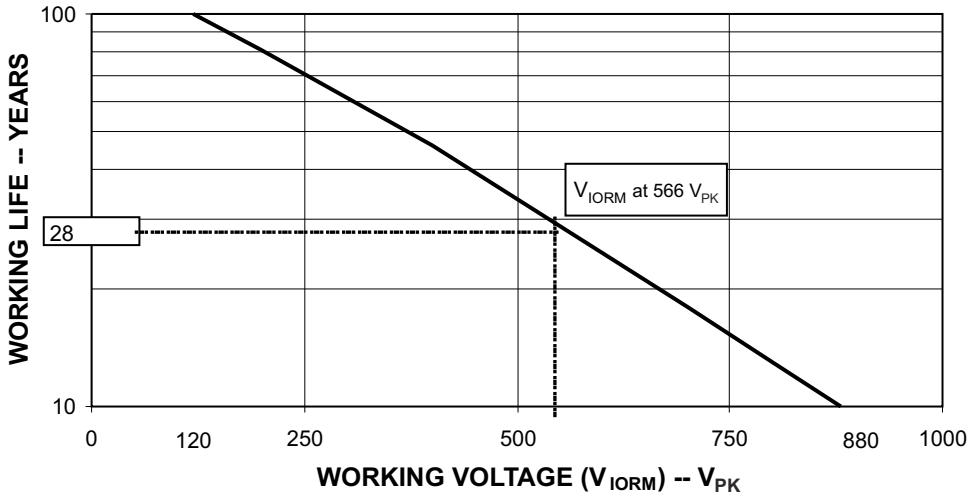


图 9-4. Time-Dependent Dielectric Breakdown Test Results

10 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, TI recommends a 0.1-µF bypass capacitor at input and output supply pins (V_{CC1} and V_{CC2}). The capacitors should be placed as close to the supply pins as possible. This device is used in applications where only a single primary-side power supply is available. Isolated power can be generated for the secondary-side with the help of integrated transformer driver.

11 Layout

11.1 Layout Guidelines

ON-chip IEC-ESD protection is good for laboratory and portable equipment but never sufficient for EFT and surge transients occurring in industrial environments. Therefore, robust and reliable bus node design requires the use of external transient protection devices. Because ESD and EFT transients have a wide frequency bandwidth from approximately 3-MHz to 3-GHz, high-frequency layout techniques must be applied during PCB design. A minimum of four layers is required to accomplish a low EMI PCB design (see 图 11-1).

- Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane, and low-frequency signal layer.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/in^2.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.
- Place the protection circuitry close to the bus connector to prevent noise transients from penetrating your board.
- Use V_{CC} and ground planes to provide low-inductance. High-frequency currents might follow the path of least inductance and not necessarily the path of least resistance.
- Design the protection components into the direction of the signal path. Do not force the transient currents to divert from the signal path to reach the protection device.
- Apply 0.1-µF bypass capacitors as close as possible to the V_{CC}-pins of transceiver, UART, and controller ICs on the board.
- Use at least two vias for V_{CC} and ground connections of bypass capacitors and protection devices to minimize effective via-inductance.
- Use 1-kΩ to 10-kΩ pullup and pulldown resistors for enable lines to limit noise currents in these lines during transient events.
- Insert pulse-proof resistors into the A and B bus lines if the TVS clamping voltage is higher than the specified maximum voltage of the transceiver bus pins. These resistors limit the residual clamping current into the transceiver and prevent it from latching up.
- While pure TVS protection is sufficient for surge transients up to 1 kV, higher transients require metal-oxide varistors (MOVs) which reduce the transients to a few hundred volts of clamping voltage, and transient blocking units (TBUs) that limit transient current to less than 1 mA.
- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.

If an additional supply voltage plane or signal layer is needed, add a second power and ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

备注

For detailed layout recommendations, see Application Note *Digital Isolator Design Guide*, SLLA284.

11.2 Layout Example

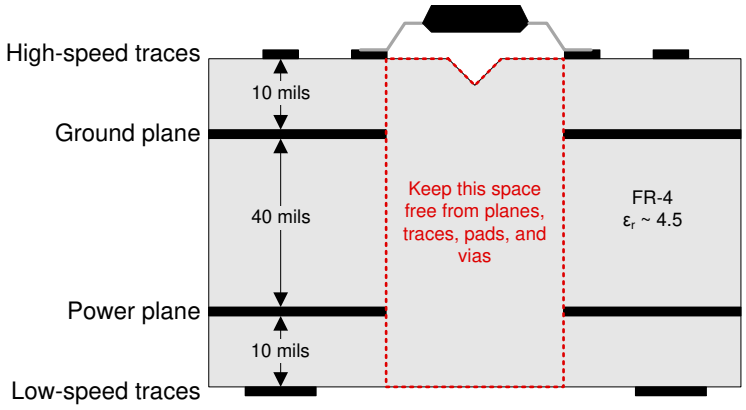


图 11-1. Recommended Layer Stack

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- *Isolated, 40-Mbps, 3.3-V to 5-V Profibus Interface* (SLUU471)
- *Digital Isolator Design Guide* (SLLA284)
- *Isolation Glossary* (SLLA353)

12.2 Community Resources

12.3 Trademarks

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12.4 静电放电警告

静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.5 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO1176TDWR	ACTIVE	SOIC	DW	16	2000	RoHS & Green	Call TI | NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ISO1176T	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

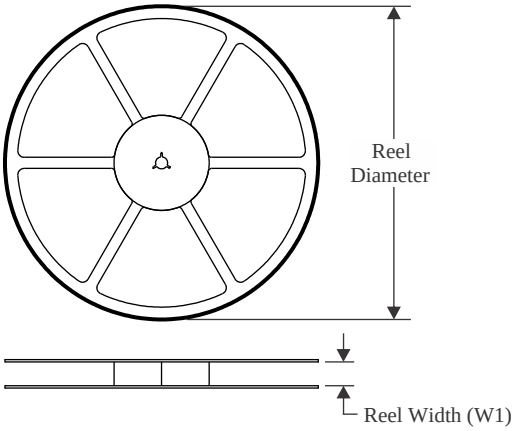
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

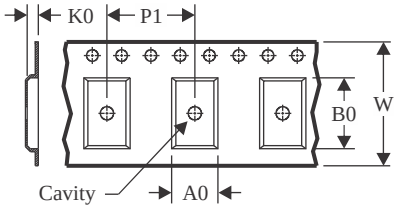
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

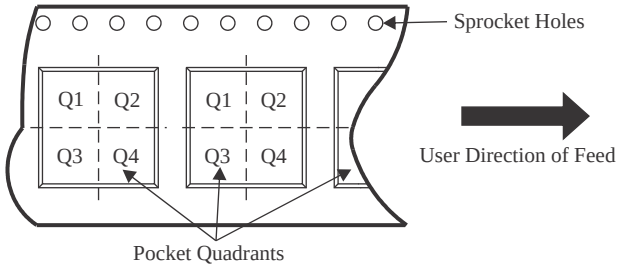


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

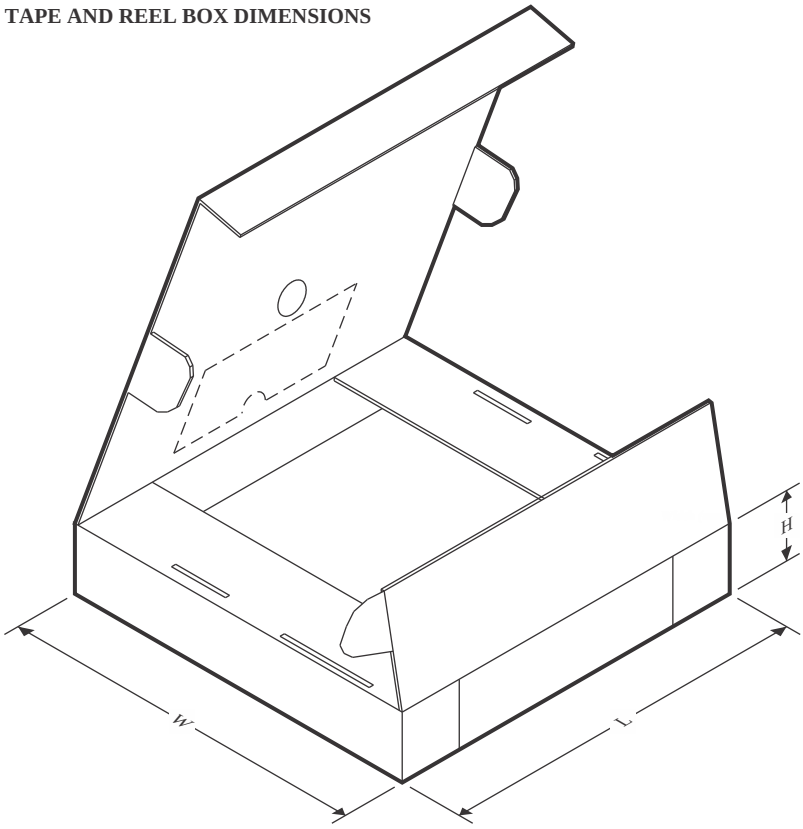
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO1176TDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

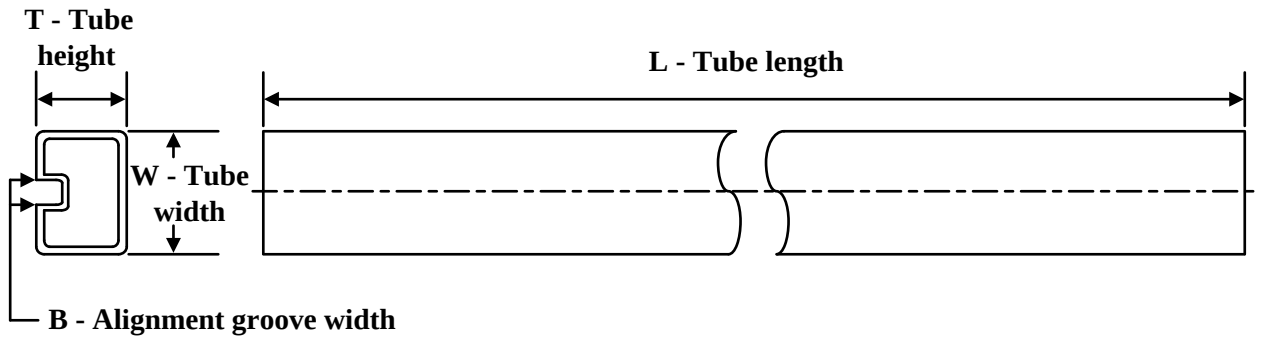
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO1176TDWR	SOIC	DW	16	2000	350.0	350.0	43.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
ISO1176TDW	DW	SOIC	16	40	506.98	12.7	4826	6.6

GENERIC PACKAGE VIEW

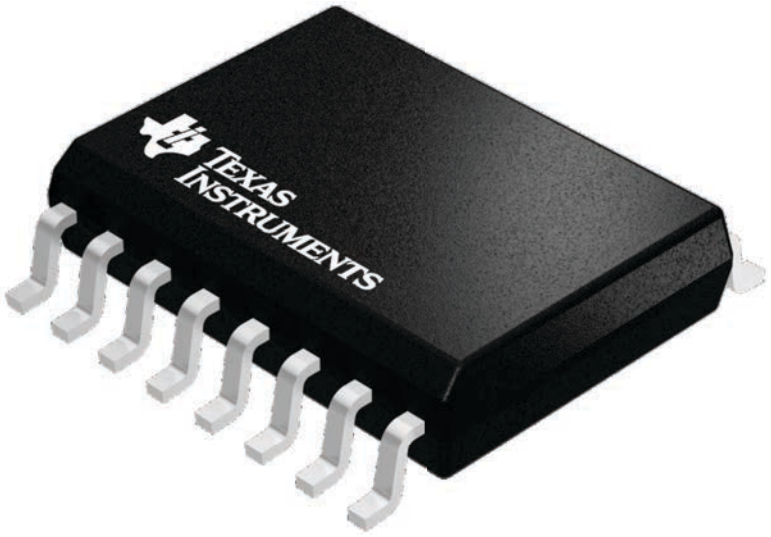
DW 16

SOIC - 2.65 mm max height

7.5 x 10.3, 1.27 mm pitch

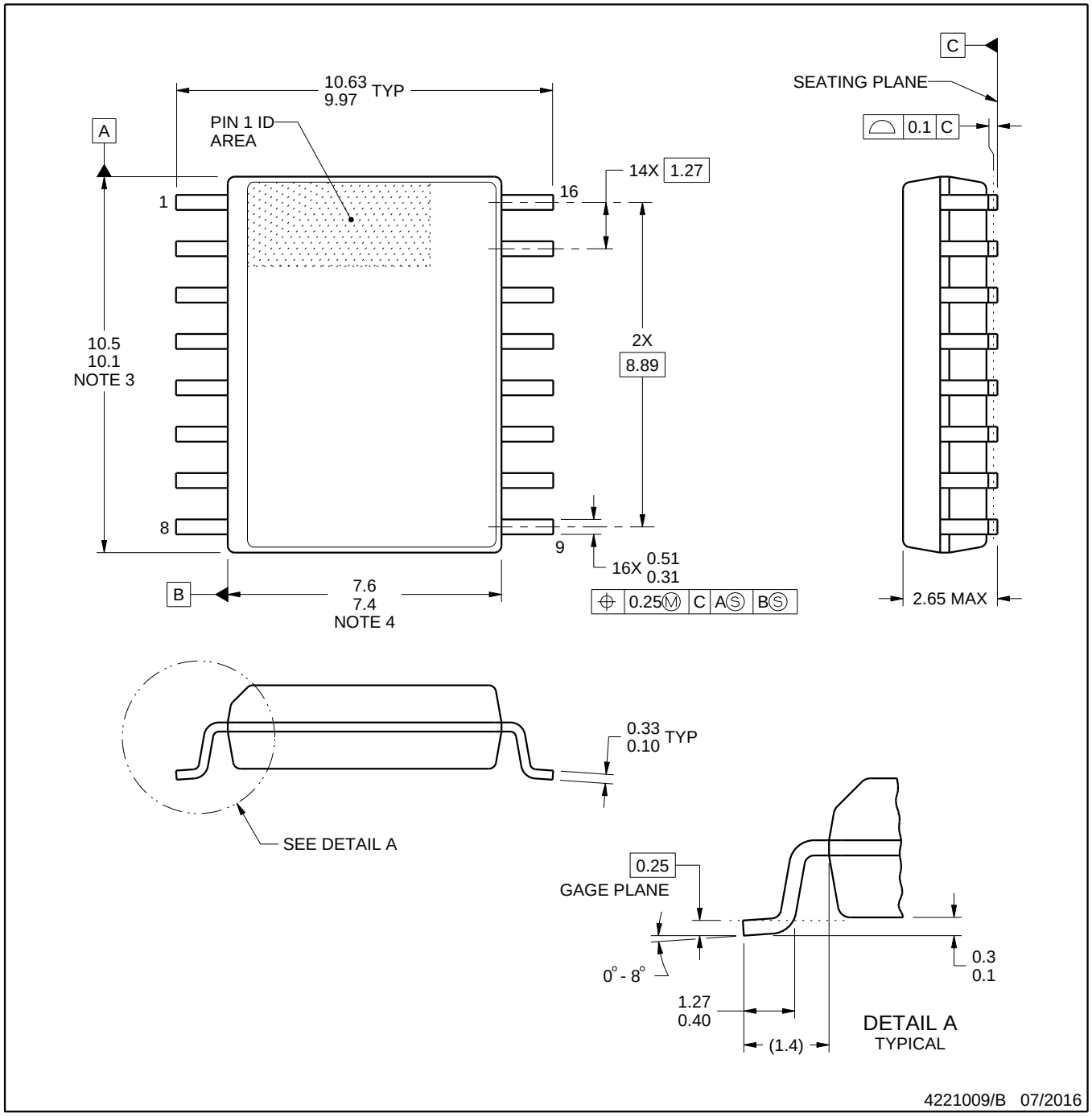
SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



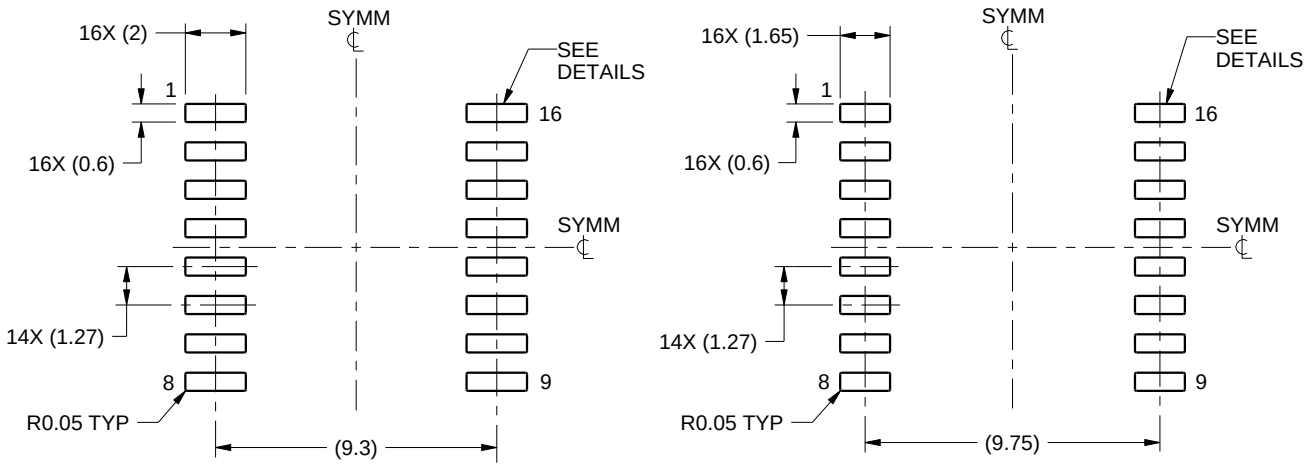
4224780/A

SOIC



NOTES:

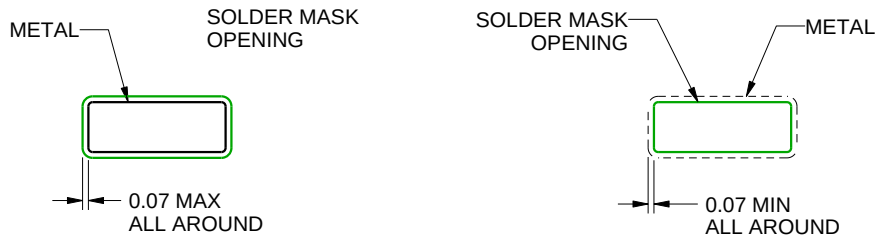
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.



IPC-7351 NOMINAL
7.3 mm CLEARANCE/CREEPAGE

HV / ISOLATION OPTION
8.1 mm CLEARANCE/CREEPAGE

LAND PATTERN EXAMPLE
SCALE:4X



NON SOLDER MASK DEFINED

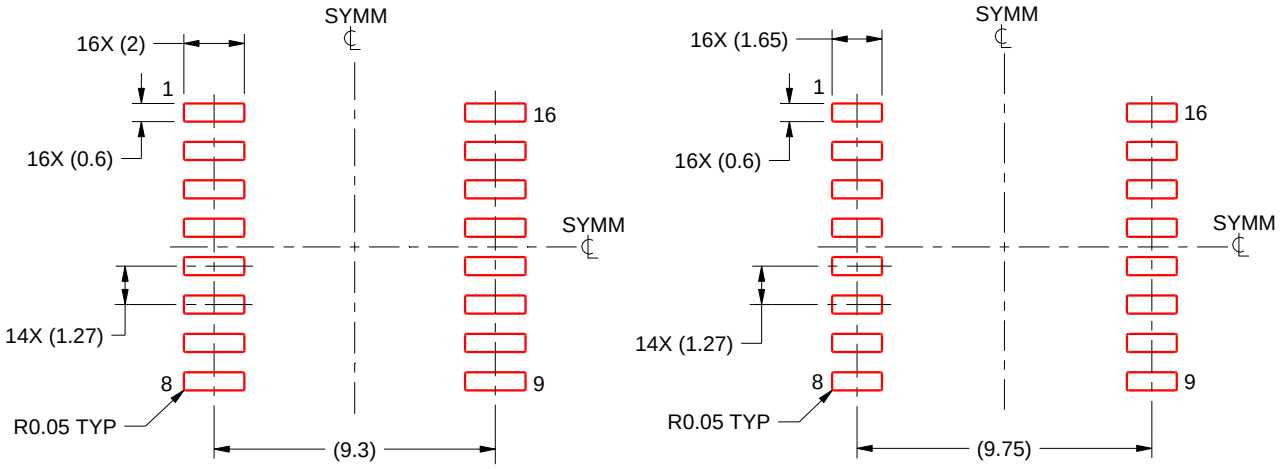
SOLDER MASK DEFINED

SOLDER MASK DETAILS

4221009/B 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



IPC-7351 NOMINAL
7.3 mm CLEARANCE/CREEPAGE

HV / ISOLATION OPTION
8.1 mm CLEARANCE/CREEPAGE

SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:4X

4221009/B 07/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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